

Switching diode

• Applications

High speed switching

• Features

- 1) Small surface mounting type.
- 2) High Speed.(trr =1.2ns Typ.)
- 3) High reliability with high surge current handling capability.
- 4) We declare that the material of product compliance with RoHS requirements.

• Construction

Silicon epitaxial planar

• Device Marking and Ordering Information

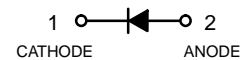
Device	Marking	Shipping
L1SS355T1G	5D	3000/Tape&Reel
L1SS355T3G	5D	10000/Tape&Reel

• Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	90	V
DC reverse voltage	V _R	80	V
Peak forward current	I _{FM}	225	mA
Mean rectifying current	I _O	100	mA
Surge current (1s)	I _{surge}	500	mA
Junction temperature	T _J	125	°C
Storage temperature	T _{stg}	-55~+125	°C

• Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditons
Forward voltage	V _F	-	-	1.2	V	I _F =100mA
Reverse current	I _R	-	-	0.1	μA	V _R =80V
Capacitance between terminals	C _T	-	-	3.0	pF	V _R =0.5V, f=1MHz
Reverse recovery time	t _{rr}	-	-	4	ns	V _R =6V, I _F =10mA, R _L =100Ω



L1SS355T1G

• Electrical characteristic curves (Ta=25°C)

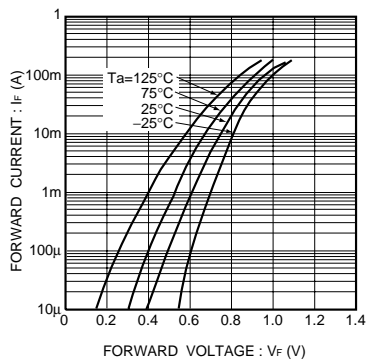


Fig.1 Forward characteristics

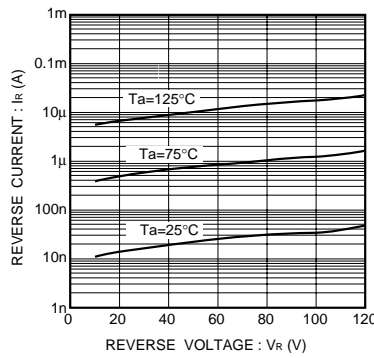


Fig.2 Reverse characteristics

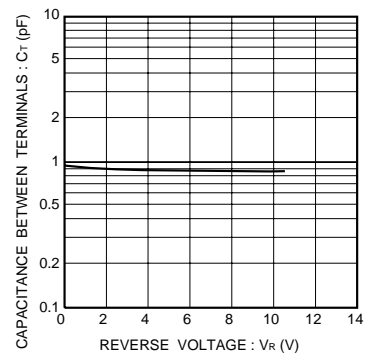


Fig.3 Capacitance between terminals characteristics

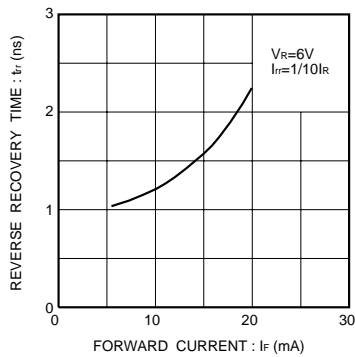


Fig.4 Reverse recovery time characteristics

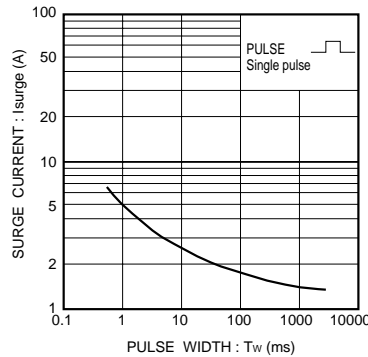


Fig.5 Surge current characteristics

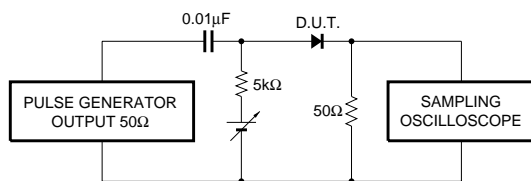
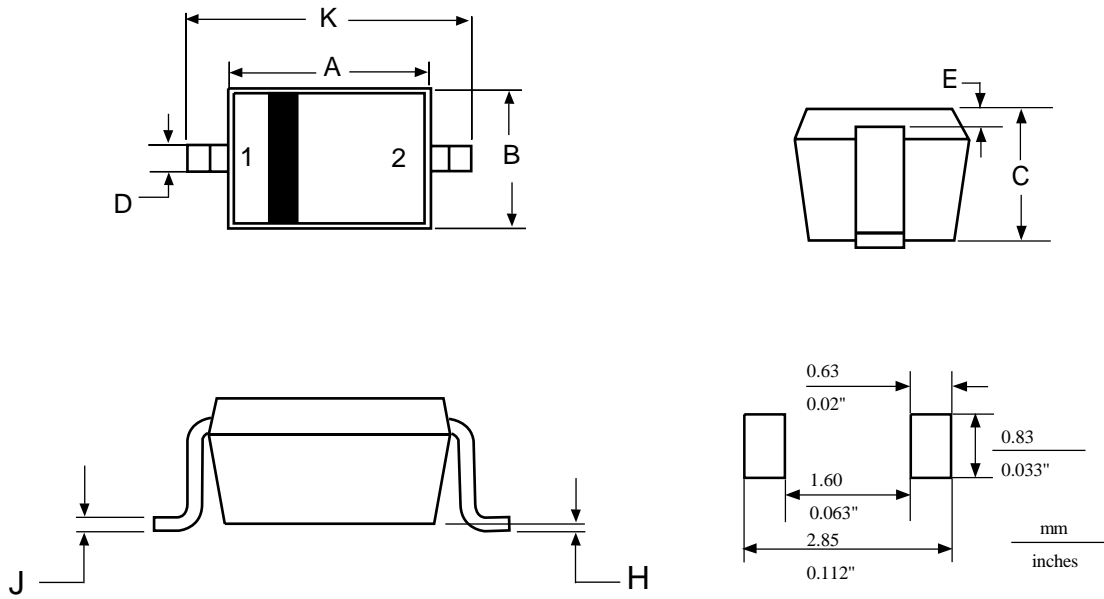


Fig.6 Reverse recovery time (t_r) measurement circuit

L1SS355T1G

SOD-323



NOTES:

1. DIMENSIONING AND TOLERANCING
PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.60	1.80	0.063	0.071
B	1.15	1.35	0.045	0.053
C	0.80	1.00	0.031	0.039
D	0.25	0.40	0.010	0.016
E	0.15 REF		0.006 REF	
H	0.00	0.10	0.000	0.004
J	0.089	0.177	0.0035	0.0070
K	2.30	2.70	0.091	0.106

PIN:1:CATHODE
2:ANODE